PATENT S/N 09/584.566

FRADEMARK OFFICE

Examiner: Jerome Jackson

-3 2001 Applicant:

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HORIZONTAL MEMORY DEVICES WITH VERTICAL GATES

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

oner for Patents Washington, D.C. 20231

Applicants have reviewed the Office Action mailed on April 27, 2001. Please amend the above-identified patent application as follows.

This response is accompanied by a Petition, as well as the appropriate fee, to obtain a one-month extension of the period for responding to the Office action, thereby moving the deadline for response from July 27, 2001 to August 27, 2001.

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect the amendment of previously pending claims 1, 7, and 14. The specific amendments to individual claims are detailed in the following marked up set of claims.

- 1. (Amended) A memory cell, comprising:
 - a source region in a horizontal substrate;
 - a drain region in the horizontal substrate;
 - a channel region separating the source and the drain regions;
- [a] an edge-defined vertical floating gate located above a portion of the channel region and separated from the channel region by a first thickness insulator material; and

at least one edge-defined vertical control gate located above another portion of the channel region and separated therefrom by a second thickness insulator material, wherein the at least one vertical control gate is parallel to and opposing the vertical floating gate, and wherein the at least one vertical control gate is separated from the vertical floating gate by an intergate dielectric.